

Contents

1 Introduction

L. C. Feldman	1
1.1 The Silicon MOSFET	1
1.2 Surface States and the Early Discoveries	3
1.3 New Technologies	4
1.4 Silicon Dioxide Growth	4
1.5 Microstructure of the Interface	5
References	8

2 Morphological Aspects of Silicon Oxidation in Aqueous Solutions

Melissa A. Hines	13
2.1 Introduction	13
2.2 Reaction Anisotropy and the Control of Atomic-Scale Morphology	14
2.3 Extreme Anisotropy: NH_4F Etching of Si(111)	15
2.4 Controlling Anisotropy: The Curious Effects of Isopropanol	18
2.5 Correlated Reactions and the Development of Mesoscale Morphologies	21
2.6 Correlated Etching: The Surprising Role of Etch Pits	21
2.7 Kinetic Structures and the Development of Etch Hillocks	24
2.8 Using Micromachined Patterns to Study Surface Chemistry	27
2.9 Conclusions and Outlook	32
References	33

3 Structural Evolution of the Silicon/Oxide Interface During Passive and Active Oxidation

F. M. Ross, J. M. Gibson	35
3.1 Introduction	35
3.2 Passive and Active Oxidation in situ in the TEM	36
3.3 Passive Oxidation as a Layer-by-Layer Process	40
3.3.1 What Can in situ Experiments Reveal About the Reaction Mechanism?	42
3.3.2 Stress, Ordering and Stoichiometry at the Interface	48
3.4 Active Oxidation as a Step-Flow Process	49

3.4.1 Kinetic Measurements of Step Nucleation and Flow	50
3.5 Control of Surface Morphology During Device Processing	54
3.6 Electron Beam Effects During in situ Electron Microscopy	55
3.7 Conclusions	56
References	57
4 Oxidation of H-Terminated Silicon	
T. Hattori, H. Nohira	61
4.1 Introduction	61
4.2 Experimental and Analytical Details	63
4.3 Initial Stage of Oxidation of H-Terminated Si Surfaces	65
4.3.1 Initial Stage of Oxidation of the H-Si(111)-1×1 Surface	65
4.3.2 Initial Stage of Oxidation of the H-Si(100)-2×1 Surface	69
4.4 Layer-by-Layer Oxidation Reaction at the Interface	72
4.4.1 Layer-by-Layer Oxidation Reaction at the SiO ₂ /Si(111) Interface	72
4.4.2 Lateral Size of Atomically Flat Interface	75
4.4.3 Effect of Initial Surface Morphology on the SiO ₂ /Si(100) Interface Structures	76
4.5 Oxidation-Induced Roughness of Oxide Surfaces	78
4.5.1 Oxidation-Induced Surface Roughness on Si(111)	78
4.5.2 Oxidation-Induced Surface Roughness on Si(100)	79
4.6 Valence Band Discontinuities at and near the SiO ₂ /Si Interface	85
4.7 Summary and Future Directions	85
References	87
5 Layer-by-Layer Oxidation of Si(001) Surfaces	
H. Watanabe, N. Miyata, M. Ichikawa	89
5.1 Introduction	89
5.2 Experimental Details	90
5.3 SREM Observation of the Initial Oxidation of Si(001)-2 × 1 Surfaces	92
5.4 Mechanism of Layer-by-Layer Oxidation	95
5.5 Kinetics of Initial Layer-by-Layer Oxidation	98
5.6 Furnace Oxidation at High Temperature	101
5.7 Summary	104
References	104
6 Atomic Dynamics During Silicon Oxidation	
A. Pasquarello, M. S. Hybertsen, R. Car	107
6.1 Introduction	107
6.2 Theoretical Approach	110
6.3 Atomic Processes During Oxidation	112

6.4	Model Structure of Si(001)-SiO ₂ Interface	116
6.5	Model of Oxidation	119
6.6	Discussion and Conclusion	121
	References	123
7	First-Principles Quantum Chemical Investigations of Silicon Oxidation	
	Krishnan Raghavachari	127
7.1	Introduction	127
7.2	Theoretical Approach	128
7.3	Water-Induced Oxidation of Si(100)-(2 × 1)	130
	7.3.1 Initial Adsorption of Water on Si(100)-(2 × 1)	131
	7.3.2 Thermodynamics of Oxygen Insertion and Aggregation	132
	7.3.3 Vibrational Spectra at 600 K – Oxygen Migration	134
	7.3.4 Higher Temperature Annealing – Oxygen Agglomeration	136
	7.3.5 Continuous Oxide Formation	139
7.4	Conclusions	139
	References	140
8	Vibrational Studies of Ultra-Thin Oxides and Initial Silicon Oxidation	
	Y.J. Chabal, M.K. Weldon, K.T. Queeney, A. Estève	143
8.1	Introduction	143
8.2	Scientific Challenges	144
	8.2.1 Spectroscopic Considerations	145
	8.2.2 Theoretical Considerations	146
8.3	Nature of Ultra-Thin Silicon Oxides and Si/SiO ₂ Interface	147
8.4	Water Oxidation of Si(100)-(2 × 1)	151
	8.4.1 Initial Oxygen Insertion and Agglomeration	151
	8.4.2 Continuous Oxide Formation	155
8.5	Conclusions	157
	References	158
9	Ion Beam Studies of Silicon Oxidation and Oxynitridation	
	W. H. Schulte, T. Gustafsson, E. Garfunkel, I. J. R. Baumvol, E. P. Gusev	161
9.1	Introduction	161
9.2	Experimental Techniques	161
	9.2.1 Ion Scattering Techniques	161
	9.2.2 Nuclear Reaction Techniques	167
	9.2.3 Isotope Tracing Techniques	171
9.3	Silicon Oxidation	172
9.4	Silicon Oxynitridation	179

9.5 Hydrogen in Ultrathin SiO ₂ Films	183
References	188
 10 Local and Global Bonding at the Si-SiO₂ Interface	
S. T. Pantelides, R. Buczko, M. Ramamoorthy, S. Rashkeev, G. Duscher, S. J. Pennycook	193
10.1 Introduction	193
10.2 The Oxidation Process and Local Bonding Arrangements	196
10.3 Global Bonding at the Interface	200
10.4 Z-Contrast Microscopy	205
10.5 Electron Energy Loss Spectroscopy	209
References	218
 11 Evolution of the Interfacial Electronic Structure During Thermal Oxidation	
D. A. Muller, J. B. Neaton	219
11.1 Introduction	219
11.2 Image Formation in STEM	221
11.3 Measuring Interface Roughness and Oxide Thickness	223
11.4 Mapping Interface States with EELS	227
11.5 Comparing Electronic Structure Calculations and EELS	234
11.6 Evolution of the Local Electronic Structure	238
11.7 Conclusions	243
References	244
 12 Structure and Energetics of the Interface Between Si and Amorphous SiO₂	
Yuhai Tu, J. Tersoff	247
12.1 Introduction	247
12.2 Method	247
12.3 Calculation and Results	249
12.4 Discussion	253
12.5 Conclusion	254
References	255
Index	257



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